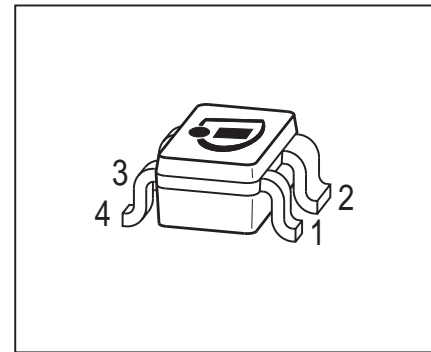
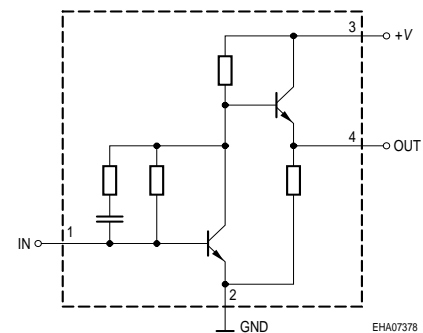


Si-MMIC-Amplifier in SIEGET® 25-Technologie

- Cascadable 50 Ω-gain block
- Unconditionally stable
- Gain $|S_{21}|^2 = 18.5$ dB at 1.8 GHz (Appl.1)
gain $|S_{21}|^2 = 22$ dB at 1.8 GHz (Appl.2)
 $IP_{3out} = +7$ dBm at 1.8 GHz ($V_D=3V$, $I_D=9.4mA$)
- Noise figure $NF = 2.2$ dB at 1.8 GHz
- Typical device voltage $V_D = 2$ V to 5 V
- Reverse isolation > 35 dB (Appl.2)
- Pb-free (RoHS compliant) package ¹⁾


Circuit Diagram

ESD (Electrostatic discharge) sensitive device, observe handling precaution!

| Type | Marking | Pin Configuration | | | | Package |
|--------|---------|-------------------|--------|-------|--------|---------|
| BGA427 | BMs | 1, IN | 2, GND | 3, +V | 4, Out | SOT343 |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|------------|-------------|------|
| Device current | I_D | 25 | mA |
| Device voltage | $V_{D,+V}$ | 6 | V |
| Total power dissipation $T_S = 120$ °C | P_{tot} | 150 | mW |
| RF input power | P_{RFIn} | -10 | dBm |
| Junction temperature | T_j | 150 | °C |
| Ambient temperature range | T_A | -65 ... 150 | |
| Storage temperature range | T_{stg} | -65 ... 150 | |

Thermal Resistance

| | | | |
|--|------------|-------|-----|
| Junction - soldering point ²⁾ | R_{thJS} | ≤ 295 | K/W |
|--|------------|-------|-----|

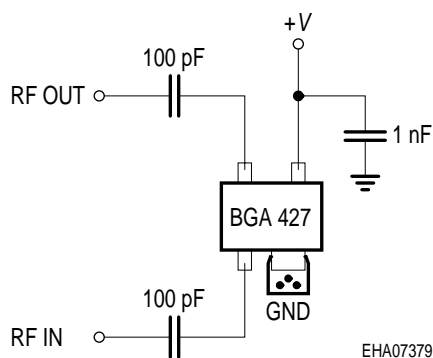
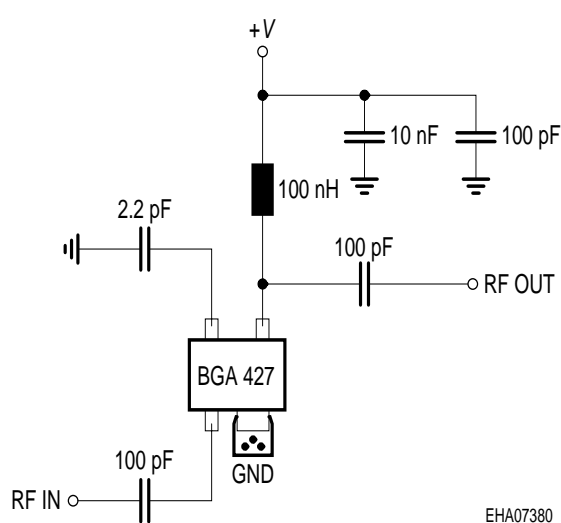
¹Pb-containing package may be available upon special request

²For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|--|--------------|--------|------------------|------|------|
| | | min. | typ. | max. | |
| AC characteristics $V_D = 3\text{ V}$, $Z_0 = 50\Omega$, Testfixture Appl.1 | | | | | |
| Insertion power gain $f = 0.1\text{ GHz}$ $f = 1\text{ GHz}$ $f = 1.8\text{ GHz}$ | $ S_{21} ^2$ | - | 27 22 18.5 | - | dB |
| Reverse isolation $f = 1.8\text{ GHz}$ | S12 | - | 22 | - | |
| Noise figure $f = 0.1\text{ GHz}$ $f = 1\text{ GHz}$ $f = 1.8\text{ GHz}$ | NF | - | 1.9 2 2.2 | - | |
| Intercept point at the output $f = 1.8\text{ GHz}$ | IP_{3out} | - | +7 | - | dBm |
| Return loss input $f = 1.8\text{ GHz}$ | RL_{in} | - | >12 | - | dB |
| Return loss output $f = 1.8\text{ GHz}$ | RL_{out} | - | >9 | - | |

Typical configuration

Appl.1

Appl.2


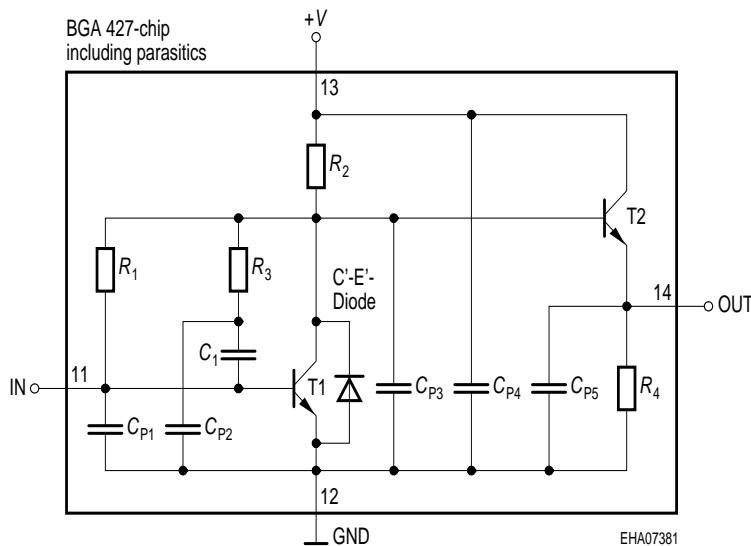
- Note: 1) Large-value capacitors should be connected from pin 3 to ground right at the device to provide a low impedance path (appl.1).
 2) The use of plated through holes right at pin 2 is essential for pc-board-applications. Thin boards are recommended to minimize the parasitic inductance to ground.

S-Parameters at $T_A = 25\text{ }^\circ\text{C}$, (Testfixture, Appl.1)

| f | S_{11} | | S_{21} | | S_{12} | | S_{22} | |
|-----|----------|-----|----------|-----|----------|-----|----------|-----|
| | MAG | ANG | MAG | ANG | MAG | ANG | MAG | ANG |

 $V_D = 3\text{V}, Z_0 = 50\Omega$

| | | | | | | | | |
|-----|--------|--------|--------|-------|--------|------|--------|-------|
| 0.1 | 0.1382 | -38.3 | 24.821 | 164.9 | 0.0022 | 50.7 | 0.6435 | 174.8 |
| 0.2 | 0.1179 | -16 | 24.606 | 158.9 | 0.0046 | 71.8 | 0.6278 | 166.9 |
| 0.5 | 0.1697 | -20.8 | 22.236 | 135.2 | 0.0104 | 83.8 | 0.54 | 147.3 |
| 0.8 | 0.1824 | -56.9 | 18.258 | 115.4 | 0.0169 | 94.8 | 0.4453 | 140.2 |
| 0.9 | 0.1782 | -69.1 | 17.152 | 109.4 | 0.0194 | 97.3 | 0.4326 | 139.4 |
| 1 | 0.176 | -80.6 | 15.786 | 104 | 0.0225 | 98.3 | 0.4129 | 138.1 |
| 1.5 | 0.1827 | -133.5 | 10.923 | 84.9 | 0.0385 | 99.7 | 0.3852 | 139.6 |
| 1.8 | 0.1969 | -156.1 | 9.029 | 77 | 0.0479 | 99.3 | 0.3917 | 139.3 |
| 1.9 | 0.2021 | -162.8 | 8.486 | 74.7 | 0.0517 | 98.9 | 0.3946 | 138.8 |
| 2 | 0.2116 | -167.7 | 8.015 | 72.3 | 0.0549 | 98.8 | 0.3991 | 138.3 |
| 2.5 | 0.2437 | 172.8 | 6.259 | 63 | 0.0709 | 97.1 | 0.4202 | 134.6 |
| 3 | 0.258 | 153.3 | 5.103 | 55 | 0.0892 | 96.9 | 0.4477 | 131 |

Spice-model BGA 427


| | |
|-------------|----------------|
| T1 | T501 |
| T2 | T501 |
| R_1 | 14.5k Ω |
| R_2 | 280 Ω |
| R_3 | 2.4k Ω |
| R_4 | 170 Ω |
| C_1 | 2.3pF |
| C_{P1} | 0.2pF |
| C_{P2} | 0.2pF |
| C_{P3} | 0.6pF |
| C_{P4} | 0.1pF |
| C_{P5} | 0.1pF |
| C'-E'-diode | T1 |

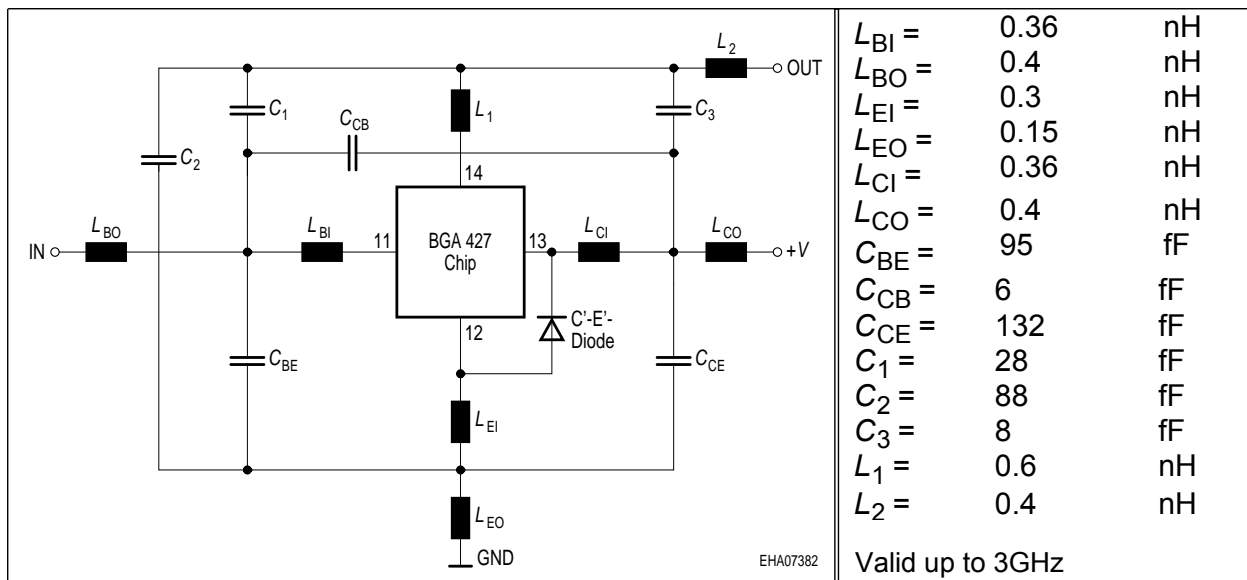
Transistor Chip Data T1 (Berkley-SPICE 2G.6 Syntax) :

| | | | | | | | | |
|-------|---------|----------|-------|---------|----------|--------|----------|----------|
| IS = | 0.21024 | fA | BF = | 83.23 | - | NF = | 1.0405 | - |
| VAF = | 39.251 | V | IKF = | 0.16493 | A | ISE = | 15.761 | fA |
| NE = | 1.7763 | - | BR = | 10.526 | - | NR = | 0.96647 | - |
| VAR = | 34.368 | V | IKR = | 0.25052 | A | ISC = | 0.037223 | fA |
| NC = | 1.3152 | - | RB = | 15 | Ω | IRB = | 0.21215 | A |
| RBM = | 1.3491 | Ω | RE = | 1.9289 | | RC = | 0.12691 | Ω |
| CJE = | 3.7265 | fF | VJE = | 0.70367 | V | MJE = | 0.37747 | - |
| TF = | 4.5899 | ps | XTF = | 0.3641 | - | VTF = | 0.19762 | V |
| ITF = | 1.3364 | mA | PTF = | 0 | deg | CJC = | 96.941 | fF |
| VJC = | 0.99532 | V | MJC = | 0.48652 | - | XCJC = | 0.08161 | - |
| TR = | 1.4935 | ns | CJS = | 0 | fF | VJS = | 0.75 | V |
| MJS = | 0 | - | XTB = | 0 | - | EG = | 1.11 | eV |
| XTI = | 3 | - | FC = | 0.99469 | - | TNOM | 300 | K |

C'-E'-Diode Data (Berkley-SPICE 2G.6 Syntax) :

| | | | | | | | | |
|------|---|----|-----|------|---|------|----|----------|
| IS = | 2 | fA | N = | 1.02 | - | RS = | 20 | Ω |
|------|---|----|-----|------|---|------|----|----------|

All parameters are ready to use, no scaling is necessary

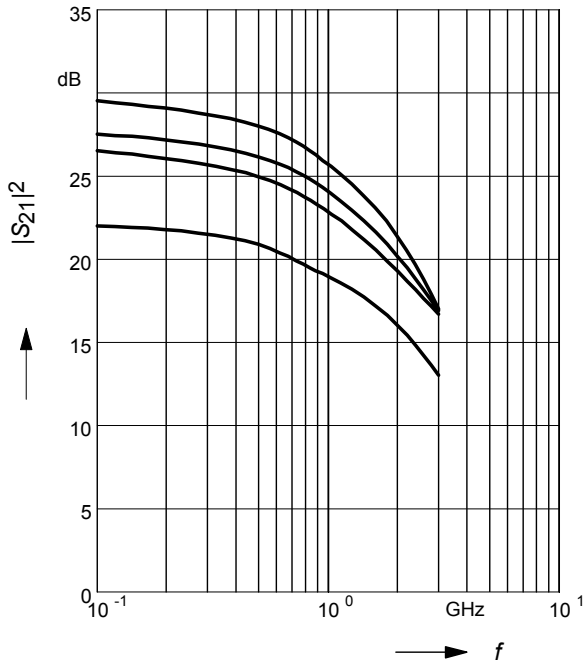
Package Equivalent Circuit:


Extracted on behalf of Infineon Technologies AG by:
 Institut für Mobil-und Satellitentechnik (IMST)

For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet:
<http://www.infineon.com/silicondiscretres>

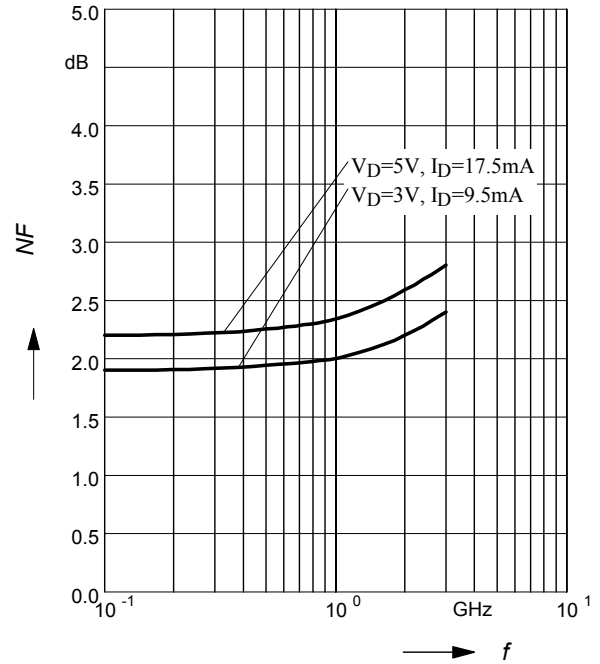
Insertion power gain $|S_{21}|^2 = f(f)$

$V_D, I_D = \text{parameter}$



Noise figure $NF = f(f)$

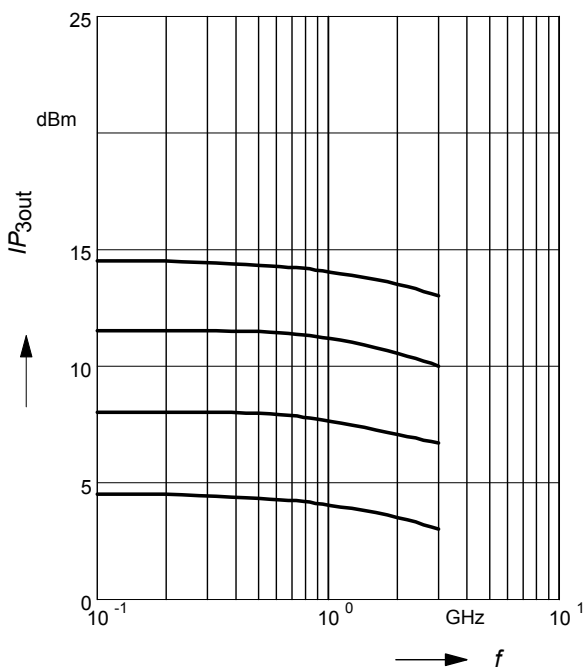
$V_D, I_D = \text{parameter}$



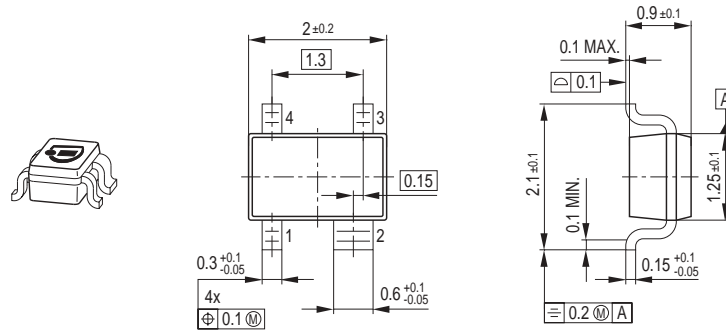
Intercept point at the output

$IP_{3out} = f(f)$

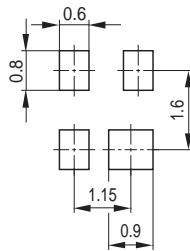
$V_D, I_D = \text{parameter}$



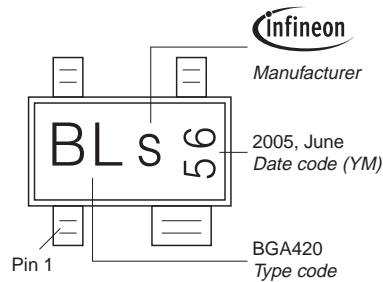
Package Outline



Foot Print

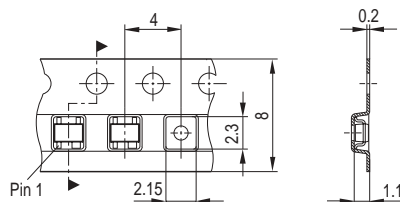


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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Infineon Technologies AG
81726 München, Germany
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